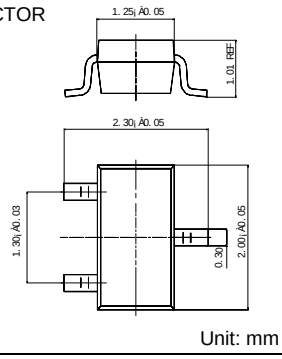
2SA1576A TRANSISTOR (PNP)

SOT-323



1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

FEATURES

Power dissipation

P_{CM} : 200 mW (Tamb=25℃)

Collector current

I_{CM} : -150 mA

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-50μA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1mA, I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-6V, I_C=-1mA	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA			-0.5	V
Transition frequency	f_T	V_{CE}=-12V, I_C=-2mA, f=30MHz		100		MHz
Collector output capacitance	C_{ob}	V_{CB}=-12V, I_E=0, f=1MHz		5		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	FQ	FR	FS

WEJ ELECTRONIC CO.